

LET9070FB

RF power transistor from the LdmoST family of N-channel enhancement-mode lateral MOSFETs

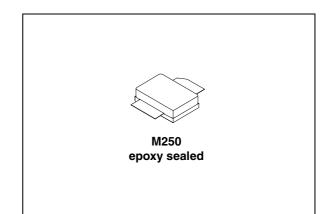
Datasheet — production data

Features

- Excellent thermal stability
- Common source configuration
- P_{OUT} (@ 28 V)= 70 W with 16 dB gain @ 945 MHz
- BeO free package
- In compliance with the 2002/95/EC European directive
- Bidirectional ESD

Description

The LET9070FB is a common source N-channel enhancement mode lateral field-effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.0 GHz. The LET9070FB is designed for high gain and broadband performance operating in common source mode at 28 V. It is ideal for base station applications requiring high linearity.





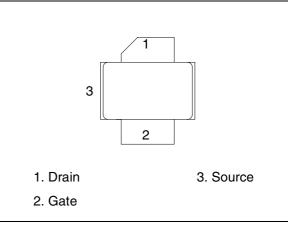


Table 1. Device summary

Order code	Package	Branding
LET9070FB	M250	LET9070FB

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1/9

This is information on a product in full production.

1 Maximum ratings

	Absolute maximum ratings (TCASE = 25°C)		
Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-source voltage	80	V
V _{GS}	Gate-source voltage	-10 to +15	V
۱ _D	Drain current		А
P _{DISS}	Power dissipation (@ T _C = 70 °C)	130	W
TJ	Max. operating junction temperature	200	°C
T _{STG}	Storage temperature	-65 to +150	°C

Table 2. Absolute maximum ratings ($T_{CASE} = 25 \ ^{\circ}C$)

	Table	3.	Thermal	data
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Symbol	Parameter	Value	Unit
R _{th(JC)}	Junction-case thermal resistance	1.0	°C/W



2 Electrical characteristics

T_C = 25 °C

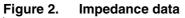
Table 4. Static

Symbol	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	$V_{GS} = 0; I_{DS} = 10 \text{ mA}$	80			V
I _{DSS}	$V_{GS} = 0; V_{DS} = 28 V$			1	μA
I _{GSS}	$V_{GS} = 5; V_{DS} = 0$			1	μA
V _{GS(Q)}	$V_{DS} = 28; I_D = 100 \text{ mA}$	2.0		5.0	V
V _{DS(ON)}	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 3 \text{ A}$		0.8	1.2	V
G _{FS}	$V_{DS} = 10 \text{ V}; \text{ I}_{D} = 3 \text{ A}$	2.5			mho
C _{ISS}	V _{GS} = 0; V _{DS} = 28 V; f = 1 MHz		78		pF
C _{OSS}	$V_{GS} = 0; V_{DS} = 28 V; f = 1 MHz$		42		pF
C _{RSS}	V _{GS} = 0; V _{DS} = 28 V; f = 1 MHz		2.7		pF

Symbol	Test conditions	Min.	Тур.	Max.	Unit
P _{OUT}	V_{DD} = 28 V; I_{DQ} = 400 mA; P_{IN} = 2.5 W; f = 945 MHz	70	80		W
G _{PS}	V_{DD} = 28 V; I_{DQ} = 400 mA; P_{OUT} = 70 W; f = 945 MHz		16		dB
h _D	V_{DD} = 28 V; I_{DQ} = 400 mA; P_{IN} = 2.5 W; f = 945 MHz	60	65		%
Load mismatch	V_{DD} = 35 V; I_{DQ} = 400 mA; P_{OUT} = 100 W; f = 945 MHz All phase angles		20:1		VSWR



3 Impedance data



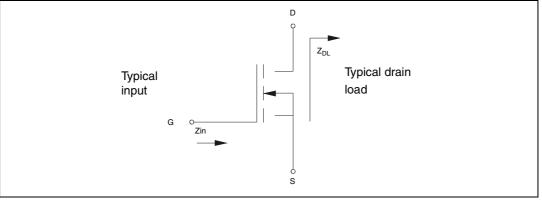


Table 6.Impedance data

Frequency	Z _{IN} (Ω)	Z _{OUT} (Ω)
945	TBD	TBD

4 Typical performance

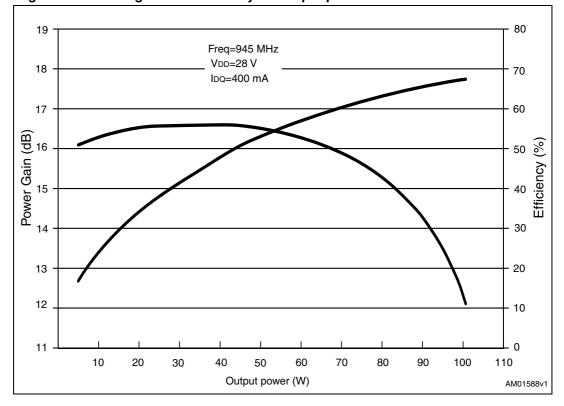


Figure 3. Power gain and efficiency vs. output power



5 Package mechanical data

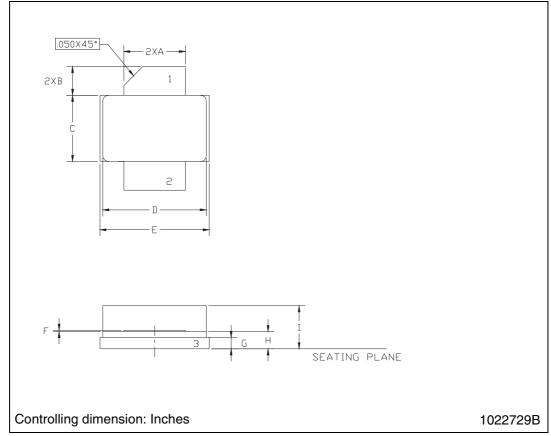
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Table 7. M250 (.230 X .360 2L N/HERM W/FLG) mechanical data								
Dim.	mm.		mm.					
	Min	Тур	Max	Min	Тур	Max		
А	5.21		5.71	0.205		0.225		
В	2.16		2.92	0.085		0.115		
С	5.59		6.09	0.220		0.240		
D	8.89		9.40	0.350		0.370		
E	9.40		9.91	0.370		0.390		
F	0.11		0.15	0.004		0.006		
G	0.89		1.14	0.035		0.045		
Н	1.45		1.70	0.057		0.067		
I	2.67		3.94	0.105		0.155		

Table 7. M250 (.230 x .360 2L N/HERM W/FLG) mechanical data





6 Revision history

Table 8.Document revision history

Date	Revision	Changes
20-Dec-2012	1	Initial release.



57

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